

KSC3503

CRT Display, Video Output

- High Voltage : V_{CEO}=300V
 Low Reverse Transfer Capacitance : C_{re}=1.8pF @ V_{CB}=30V



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	300	V
V _{CEO}	Collector-Emitter Voltage	300	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	100	mA
I _{CP}	Collector Current (Pulse)	200	mA
P _C	Collector Dissipation (T _C =25°C)	7	W
P _C	Collector Dissipation (T _A =25°C)	1.2	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	300			V
BV _{CEO}	Collecto- Emitter Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	300			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 200V, I_{E} = 0$			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			0.1	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 10V, I_{C} = 10mA$	40		320	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 20 \text{mA}, I_B = 2 \text{mA}$			0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 20 \text{mA}, I_B = 2 \text{mA}$			1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 30V, I_{C} = 10mA$		150		MHz
C _{ob}	Output Capacitance	V _{CB} = 30V, f = 1MHz		2.6		pF
C _{re}	Reverse Transfer Capacitance	V _{CB} = 30V, f = 1MHz		1.8		pF

h_{FE} Classification

Classification	С	D	Е	F
h _{FE}	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320

Typical Characteristics

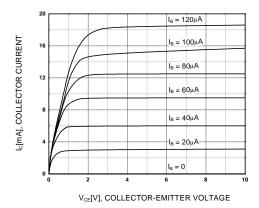
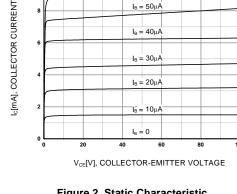


Figure 1. Static Characteristic



I_B = 60μA

Figure 2. Static Characteristic

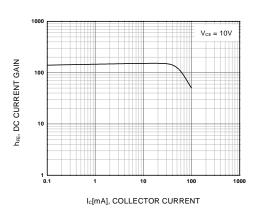


Figure 3. DC current Gain

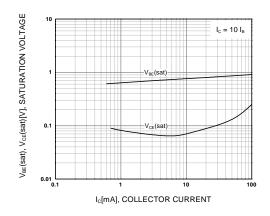


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

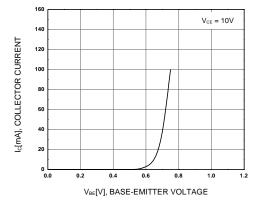


Figure 5. Base-Emitter On Voltage

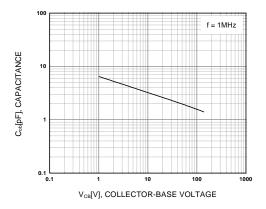


Figure 6. Collector Output Capacitance

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Typical Characteristics (Continued)

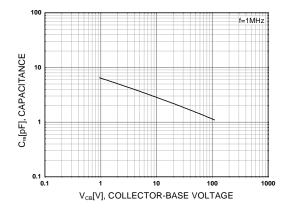


Figure 7. Reverse Transfer Capacitance

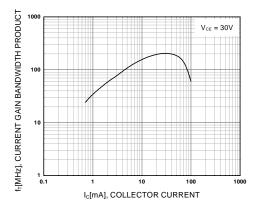


Figure 8. Current Gain Gandwidth Product

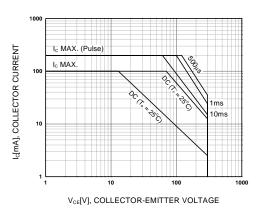


Figure 9. Safe Operating Area

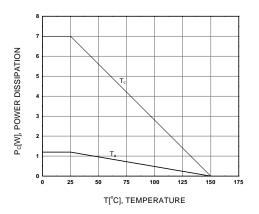
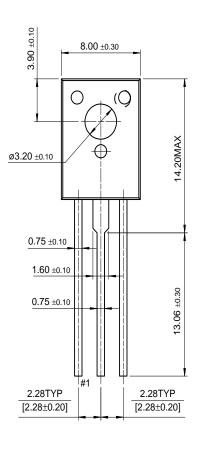
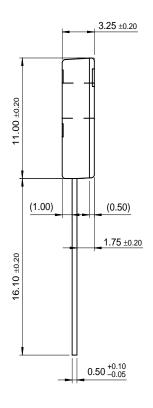


Figure 10. Power Derating

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Dimensions in Millimeters

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